

ABSTRACT OF THE DISCLOSURE

In the method, a cap wafer surface is lithographically etched at time of fabrication, so that a raised ridge onto which bonding material is placed is formed near a perimeter of a desired cavity region. This is done in order to reduce the bonding area between the cap wafer and electronic device wafers, so as to provide a better defined standoff. In another aspect of the method, the cap wafer surface is lithographically etched to form recesses or trenches near the perimeter of a cavity region, each recess being filled with a sealing material, and polished if necessary to be flush with the cap wafer surface. Thereafter, the cap wafer surface is etched so that the filled recesses become the raised ridges which are used to bond a cap wafer to an electronic device wafer.

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